

BC337,126

BC337,126 Information

	Part Number	BC337,126
www.ibeisener.com	Manufacturer	NXP
	Category	Discrete Sen Transistors -
	Description	TRANS NP
	Package	ТО-226-3, Т
		For the prici
		us

t Number	DC557,120
nufacturer	NXP
egory	Discrete Semiconductor Products Transistors - Bipolar (BJT) - Single
cription	TRANS NPN 45V 0.5A TO-92
kage	TO-226-3, TO-92-3 (TO-226AA) (Formed Leads)
	For the pricing/inventory/lead time, please contact
	us
	Website: https://www.heisener.com
	E-mail: salesdept@heisener.com



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Certified Quality

For Reference Only

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.



BC337,126 Specifications

Manufacturer Part NumberBC337,126ManufacturerNXPCategoryDiscrete Semiconductor ProductsTransistor - Bipolar (BJT) - SinglePackageTO-226-3, TO-92-3 (TO-226AA) (Formed Leads)Series-Transistor TypeNPNCurrent - Collector (Ic) (Max)500mAVoltage - Collector Emitter Breakdown (Max)45VVce Saturation (Max) @ Ib, Ic700mV @ 50mA, 500mACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce100 @ 100mA, 1VPower - Max625mWFrequency - Transition100MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 (TO-226AA) (Formed Leads)Supplier Device PackageTO-92-3			
CategoryDiscrete Semiconductor ProductsCategoryTransistors - Bipolar (BJT) - SinglePackageTO-226-3, TO-92-3 (TO-226AA) (Formed Leads)Series-Transistor TypeNPNCurrent - Collector (Lc) (Max)500mAVoltage - Collector Emitter Breakdown (Max)45VVcc Saturation (Max) @ Ib, Ic700mV @ 50mA, 500mACurrent - Collector Cutoff (Max)100nA (ICBO)DC current Gain (hFE) (Min) @ Ic, Vce100 @ 100mA, 1VPower - Max625mWFrequency - Transition100MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 (TO-226AA) (Formed Leads)Supplier Device PackageTO-92-3	Manufacturer Part Number	BC337,126	
Transitors - Bipolar (BJT) - SinglePackageTro.226-3, TO-92-3 (TO-226AA) (Formed Leads)Series-Transistor TypeNPNCurrent - Collector (Ic) (Max)500mAVoltage - Collector Emitter Breakdown (Max)45VVce Saturation (Max) @ Ib, Ic700mV @ 50mA, 500mACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce100 @ 100mA, 1VPower - Max625mWFrequency - Transition100MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 (TO-226AA) (Formed Leads)Supplier Device PackageTO-92-3	Manufacturer	NXP	
PackageTO-226-3, TO-92-3 (TO-226AA) (Formed Leads)Series-Transistor TypeNPNCurrent - Collector (Ic) (Max)500mAVoltage - Collector Emitter Breakdown (Max)45VVce Saturation (Max) @ Ib, Ic700mV @ 50mA, 500mACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce100 @ 100mA, 1VPower - Max625mWFrequency - Transition100MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 (TO-226AA) (Formed Leads)Supplier Device PackageTO-92-3	Category	Discrete Semiconductor Products	
Series-Transistor TypeNPNCurrent - Collector (Ic) (Max)500mAVoltage - Collector Emitter Breakdown (Max)45VVcc Saturation (Max) @ Ib, Ic700mV @ 50mA, 500mACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min @ Ic, Vce100 @ 100mA, 1VPower - Max625mWFrequency - Transition100MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 (TO-226AA) (Formed Leads)Supplier Device PackageTO-92-3		Transistors - Bipolar (BJT) - Single	
Transistor TypeNPNCurrent - Collector (Lo) (Max)500mAVoltage - Collector Emitter Breakdown (Max)45VVce Saturation (Max) @ Ib, Ic700mV @ 50mA, 500mACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min @ Ic, Vce100 @ 100mA, 1VPower - Max625mWFrequency - Transition100MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 (TO-226AA) (Formed Leads)Supplier Device PackageTO-92-3	Package	TO-226-3, TO-92-3 (TO-226AA) (Formed Leads)	
Current - Collector (Ic) (Max)500mAVoltage - Collector Emitter Breakdown (Max)45VVce Saturation (Max) @ Ib, Ic700mV @ 50mA, 500mACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce100 @ 100mA, 1VPower - Max625mWFrequency - Transition100MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 (TO-226AA) (Formed Leads)Supplier Device PackageTO-92-3	Series	-	
Voltage - Collector Emitter Breakdown (Max)45VVce Saturation (Max) @ Ib, Ic700mV @ 50mA, 500mACurrent - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce100 @ 100mA, 1VPower - Max625mWFrequency - Transition100MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 (TO-226AA) (Formed Leads)Supplier Device PackageTO-92-3	Transistor Type	NPN	
Yee Saturation (Max) @ Ib, Ic 700mV @ 50mA, 500mA Current - Collector Cutoff (Max) 100nA (ICBO) DC Current Gain (hFE) (Min) @ Ic, Vce 100 @ 100mA, 1V Power - Max 625mW Frequency - Transition 100MHz Operating Temperature 150°C (TJ) Mounting Type Through Hole Package / Case TO-226-3, TO-92-3 (TO-226AA) (Formed Leads) Supplier Device Package TO-92-3	Current - Collector (Ic) (Max)	500mA	
Current - Collector Cutoff (Max)100nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce100 @ 100mA, 1VPower - Max625mWFrequency - Transition100MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 (TO-226AA) (Formed Leads)Supplier Device PackageTO-92-3	Voltage - Collector Emitter Breakdown (Max)	45V	
DC Current Gain (hFE) (Min) @ Ic, Vce100 @ 100mA, 1VPower - Max625mWFrequency - Transition100MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 (TO-226AA) (Formed Leads)Supplier Device PackageTO-92-3	Vce Saturation (Max) @ Ib, Ic	700mV @ 50mA, 500mA	
Power - Max625mWFrequency - Transition100MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 (TO-226AA) (Formed Leads)Supplier Device PackageTO-92-3	Current - Collector Cutoff (Max)	100nA (ICBO)	
Frequency - Transition100MHzOperating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 (TO-226AA) (Formed Leads)Supplier Device PackageTO-92-3	DC Current Gain (hFE) (Min) @ Ic, Vce	100 @ 100mA, 1V	
Operating Temperature150°C (TJ)Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 (TO-226AA) (Formed Leads)Supplier Device PackageTO-92-3	Power - Max	625mW	
Mounting TypeThrough HolePackage / CaseTO-226-3, TO-92-3 (TO-226AA) (Formed Leads)Supplier Device PackageTO-92-3	Frequency - Transition	100MHz	
Package / CaseTO-226-3, TO-92-3 (TO-226AA) (Formed Leads)Supplier Device PackageTO-92-3	Operating Temperature	150°C (TJ)	
Supplier Device Package TO-92-3	Mounting Type	Through Hole	
	Package / Case	TO-226-3, TO-92-3 (TO-226AA) (Formed Leads)	
Report errors?	Supplier Device Package	TO-92-3	
		Report errors?	

BC337,126 Guarantees



Quality Guarantees

We provide 90 days warranty. * If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.

SERVICE GUARANTEE

Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.



If you have any question about BC337,126, please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com